

AUG 06 1990

INTERNATIONAL RECTIFIER **IOR**

150HF(R)/200HF(R)... SERIES

150/200 Amp Average Medium Power Silicon Rectifier Diodes

Features

- Wide current range
- High surge current capabilities
- Types up to 1600V V_{RRM}
- Stud cathode and stud anode version
- Standard JEDEC types
- Diffused junction

Description

This range of medium power general purpose rectifier diodes is designed for battery chargers, converters, power supplies, machine tool controls.



Major ratings and characteristics

Parameter	150HF...	200HF...	Units
$I_{F(AV)}$	150	200	A
@ T_c	125	125	°C
I_{FSM} @ 50Hz	2900	3700	A
@ 60Hz	3040	3870	A
I^2t @ 50Hz	42050	68450	A ² s
@ 60Hz	38400	62500	A ² s
V_{RRM}	200 to 1600		V
T_J	-40 to 180		°C

ELECTRICAL SPECIFICATIONS

Voltage ratings

Type number	Voltage code	V_{RRM} , maximum repetitive peak reverse voltage $T_J = T_J \text{ Max.}$	V_{RSM} , maximum non-repetitive peak reverse voltage $T_J = T_J \text{ Max.}$	I_{RRM} Max @ rated V_{RRM} $T_J = T_J \text{ Max.}$
		(V)	(V)	(mA)
150HF(R)20/200HF(R)20	20	200	300	15
150HF(R)40/200HF(R)40	40	400	500	15
150HF(R)60/200HF(R)60	60	600	700	15
150HF(R)80/200HF(R)80	80	800	900	15
150HF(R)100/200HF(R)100	100	1000	1100	15
150HF(R)120/200HF(R)120	120	1200	1300	15
150HF(R)140/200HF(R)140	140	1400	1500	15
150HF(R)160/200HF(R)160	160	1600	1700	15

Forward Conduction

Parameters	150HF	200HF	Units	Conditions	
$I_{F(AV)}$ @ T_C Maximum average forward current	150	200	A	180° Sine Conduction angle	
	125	125	°C		
$I_{F(RMS)}$ Maximum RMS current	235	314	A		
I_{FSM} Maximum peak, one-cycle non-repetitive forward current Initial $T_J = T_J \text{ max.}$	2900	3700	A	$t = 10\text{ms}$	100% V_{RRM} reapplied
	3040	3870	A	$t = 8.3\text{ms}$	
	3450	4400	A	$t = 10\text{ms}$	No voltage reapplied
	3610	4610	A	$t = 8.3\text{ms}$	
I^2t Maximum I^2t for fusing Initial $T_J = T_J \text{ max.}$	42050	68450	A ² s	$t = 10\text{ms}$	100% V_{RRM} reapplied
	38400	62490	A ² s	$t = 8.3\text{ms}$	
	59470	96800	A ² s	$t = 10\text{ms}$	No voltage reapplied
	54290	88370	A ² s	$t = 8.3\text{ms}$	
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	594.7	968	kA ² √s	I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$; $0.1 \leq t_x \leq 10\text{ms}$	
$V_{F(TO)}$ High-level of threshold voltage	1.14	1.04	V	$T_J = 180^\circ\text{C}$, $(\pi \times I_{(AV)}) < I < 20 \times \pi \times I_{(AV)}$	
$V_{F(TO)2}$ Low-level of threshold voltage	0.95	0.85	V	$T_J = 180^\circ\text{C}$, $(16.7\% \times \pi \times I_{(AV)}) < I < \pi \times I_{(AV)}$	
r_{th1} High-level of forward slope resistance	0.78	0.59	mΩ	$T_J = 180^\circ\text{C}$, $(\pi \times I_{(AV)}) < I < 20 \times \pi \times I_{(AV)}$	
r_{th2} Low-level of forward slope resistance	1.13	0.85	mΩ	$T_J = 180^\circ\text{C}$, $(16.7\% \times \pi \times I_{(AV)}) < I < \pi \times I_{(AV)}$	
V_{FM} Maximum forward voltage drop	-	1.45	V	$T_J = 25^\circ\text{C}$, $I_{FM} = 628\text{A}_{pk}$	
	1.53	-	V	$T_J = 25^\circ\text{C}$, $I_{FM} = 471\text{A}_{pk}$	

Thermal and Mechanical Specifications

Parameters	150HF	200HF	Units	Conditions	
T_J Junction temperature range	-40 to 180		°C		
T_{stg} Storage temperature range	-55 to 180		°C		
R_{thJC} Max. thermal resistance junction to case	0.22	0.17	K/W	DC operation	
R_{thCS} Max. thermal resistance, case to heatsink	0.08	0.08	K/W	Mounting surface, smooth, flat and greased	
wt Approximate weight	100		g		
T Mounting Torque ± 10%	10		Nm		
Max. constant accel.	6000 g		m/s ²	Stud outwards	
Case style	DO-205AC (DO-30) / DO-205AA (DO-8)				

ΔR_{th} Conduction (per junction)

(The following table shows the increment of thermal resistance R_{thJ-C} when devices operate at different conduction angles than DC.)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	150HF...	200HF...	150HF...	200HF...		
180°	0.045	0.045	0.037	0.037	K/W	
120°	0.056	0.056	0.061	0.061	K/W	
90°	0.073	0.073	0.079	0.079	K/W	
60°	0.102	0.102	0.105	0.105	K/W	
30°	0.154	0.154	0.156	0.156	K/W	

ORDERING INFORMATION TABLE

Device Code



- 1** - Basic Part Number
- 2** - Missing = Cathode-to-case
R = Anode-to-case
- 3** - Voltage code (See Voltage ratings Table)
- 4** - Outline (See Table)
- 5** - Leads and terminal designator:
S = Isolated lead
B = Flag terminal
None = Non isolated lead

OUTLINE

None = Stud base UNF threads
DO-30 (DO-205AC) 1/2" 20 UNF-2A

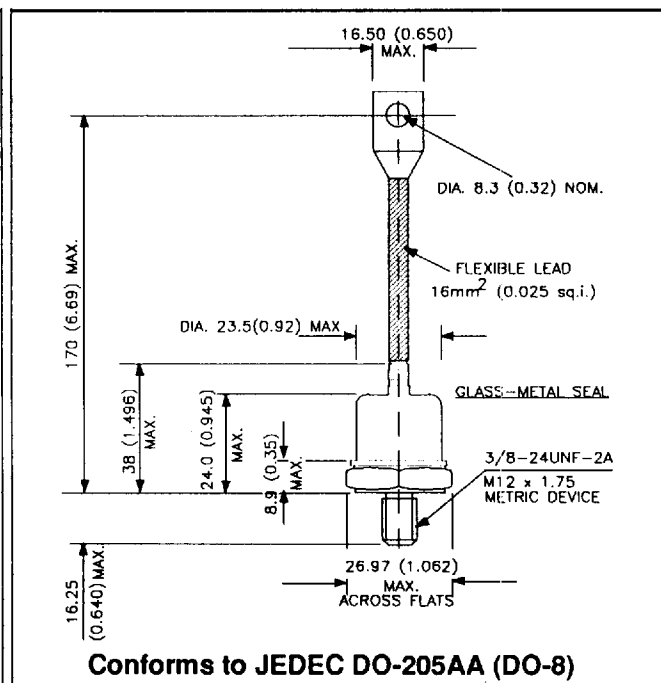
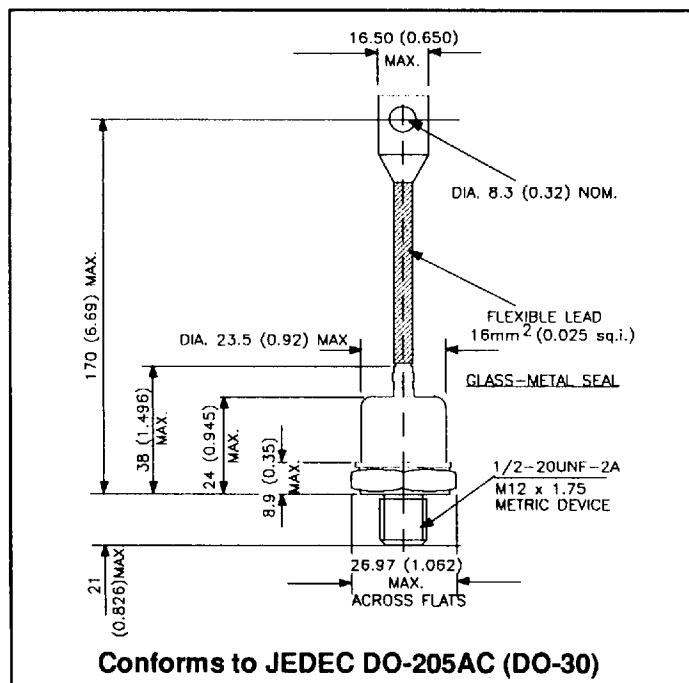
M = Stud base metric threads
DO-30 (DO-205AC) M12 x 1.75

W = Stud base UNF threads
DO-8 (DO-205AA) 3/8" 24 UNF-2A
(Contact Factory)

F = Flat base (Contact Factory)

K = Flat square base (Contact Factory)

OUTLINE TABLE



All dimensions in millimetres (inches)



Fig. 1 - CURRENT RATINGS CHARACTERISTICS

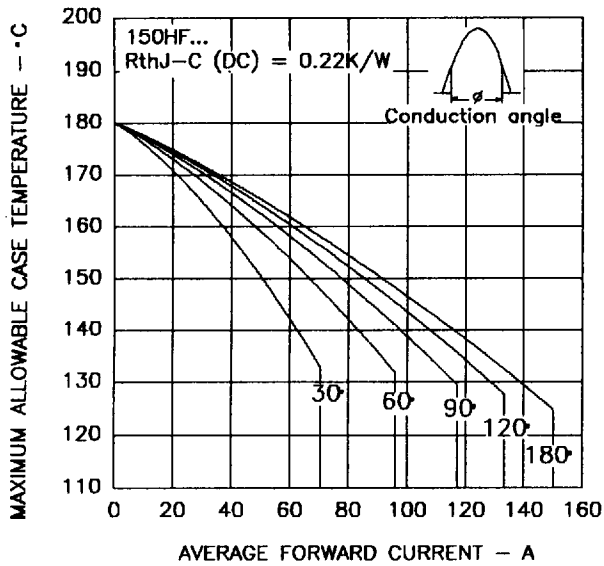


Fig. 2 - CURRENT RATINGS CHARACTERISTICS

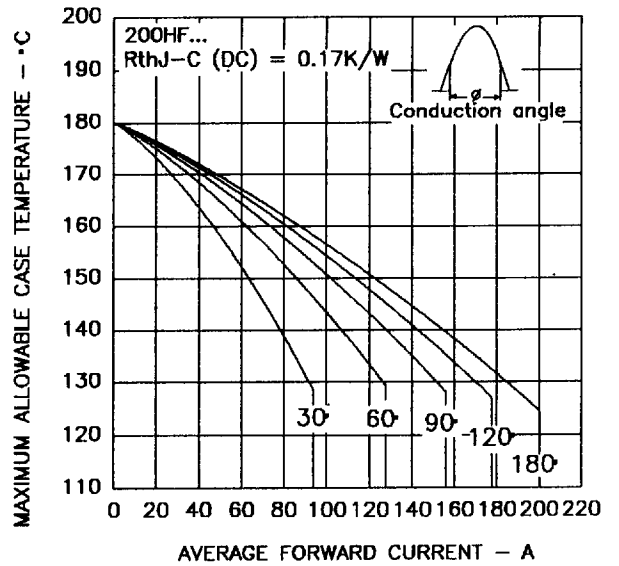


Fig. 3 - CURRENT RATINGS CHARACTERISTICS

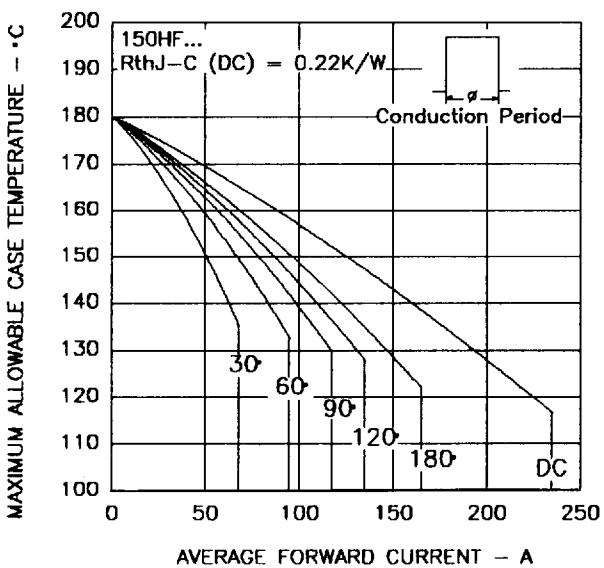


Fig. 4 - CURRENT RATINGS CHARACTERISTICS

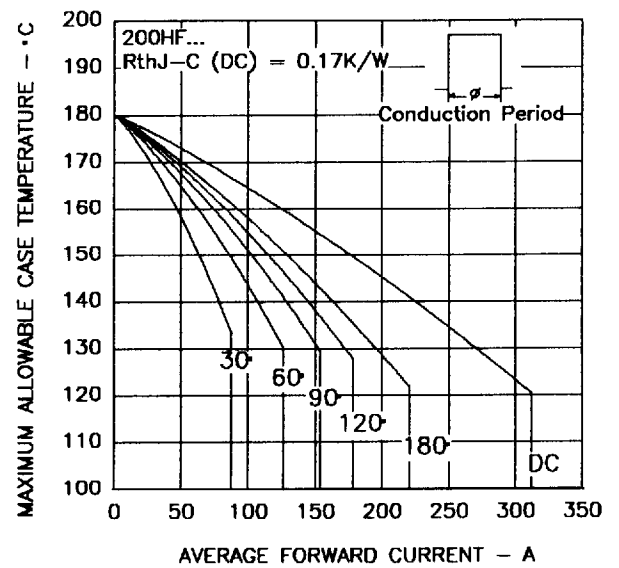


Fig. 5 - FORWARD POWER LOSS CHARACTERISTICS

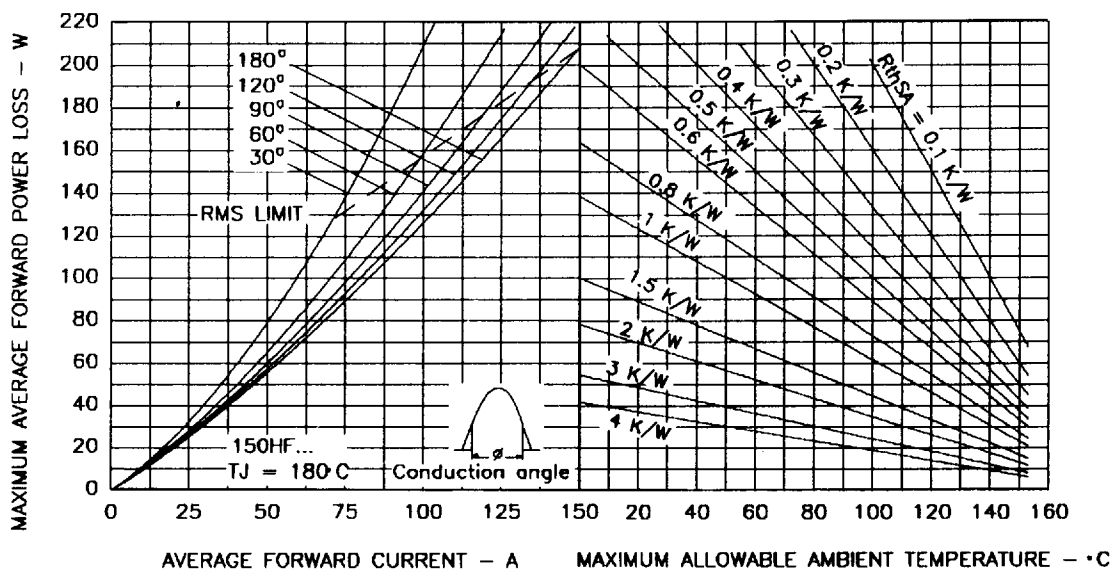


Fig. 6 - FORWARD POWER LOSS CHARACTERISTICS

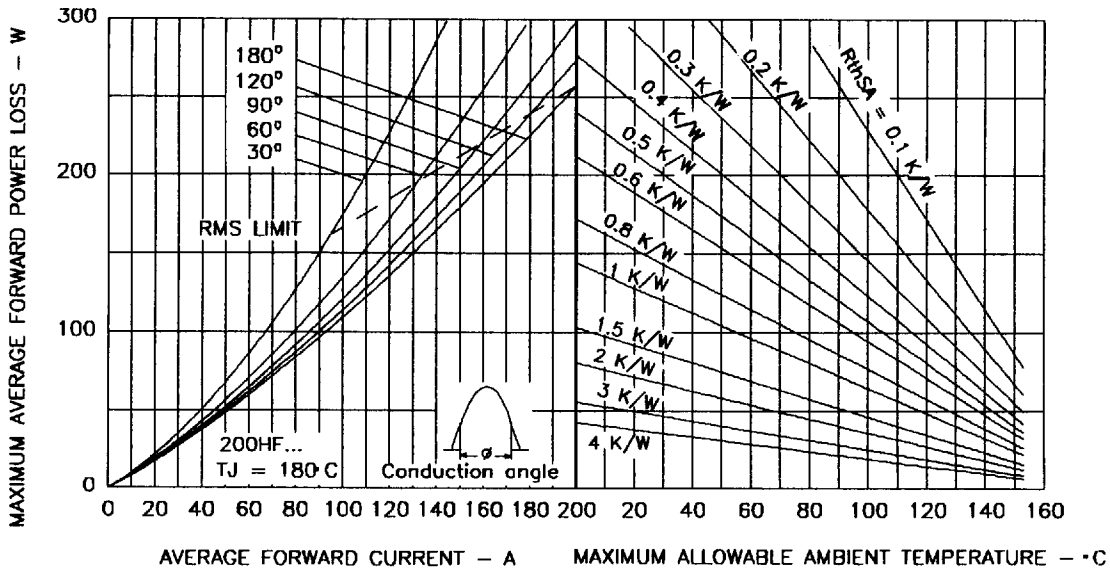


Fig. 7 - FORWARD POWER LOSS CHARACTERISTICS

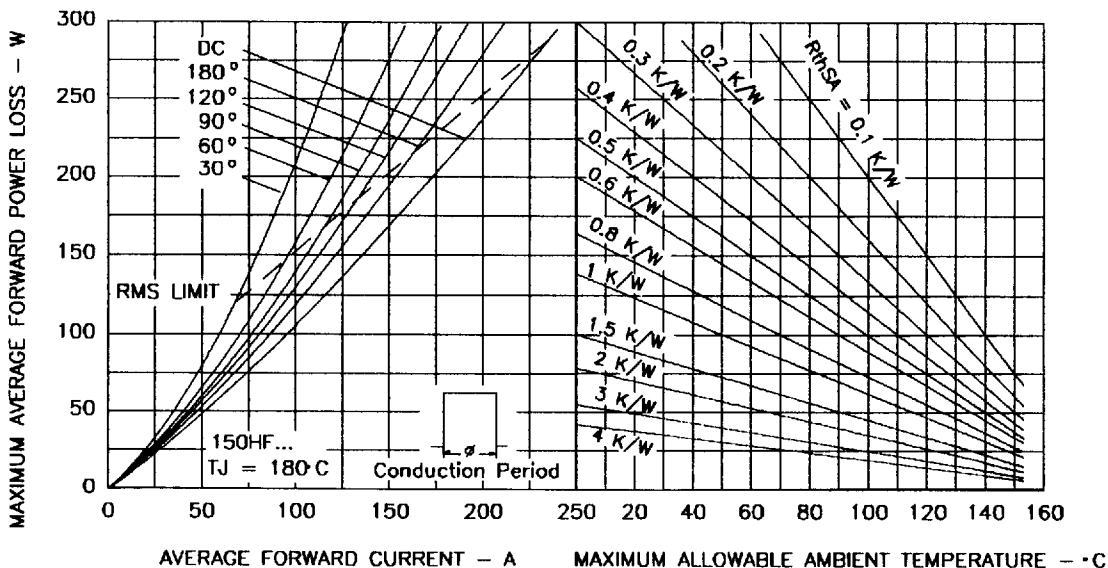
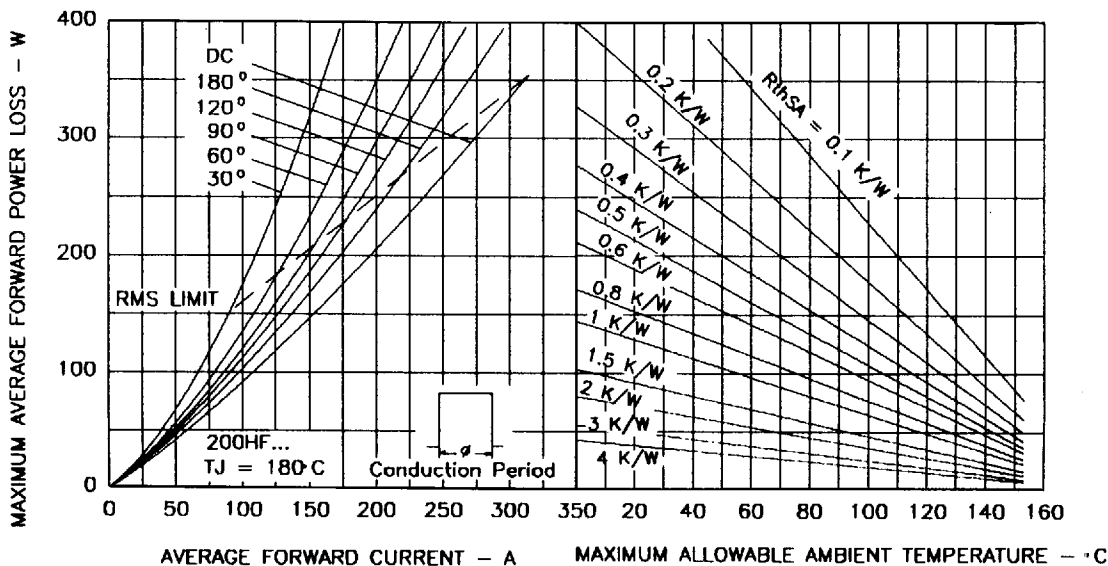


Fig. 8 - FORWARD POWER LOSS CHARACTERISTICS



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Fig. 9 - MAXIMUM NON-REPETITIVE SURGE CURRENT

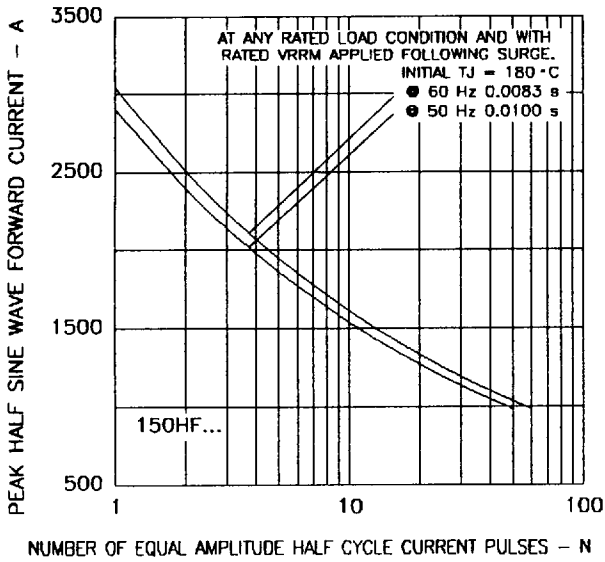


Fig. 10 - MAXIMUM NON-REPETITIVE SURGE CURRENT

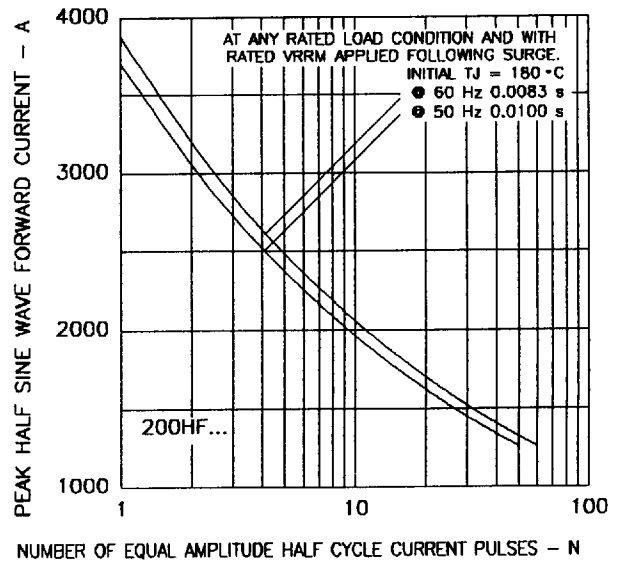


Fig. 11 - MAXIMUM NON-REPETITIVE SURGE CURRENT

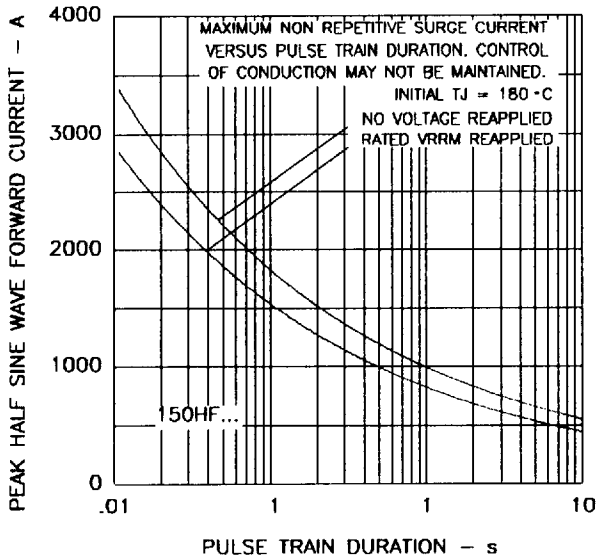


Fig. 12 - MAXIMUM NON-REPETITIVE SURGE CURRENT

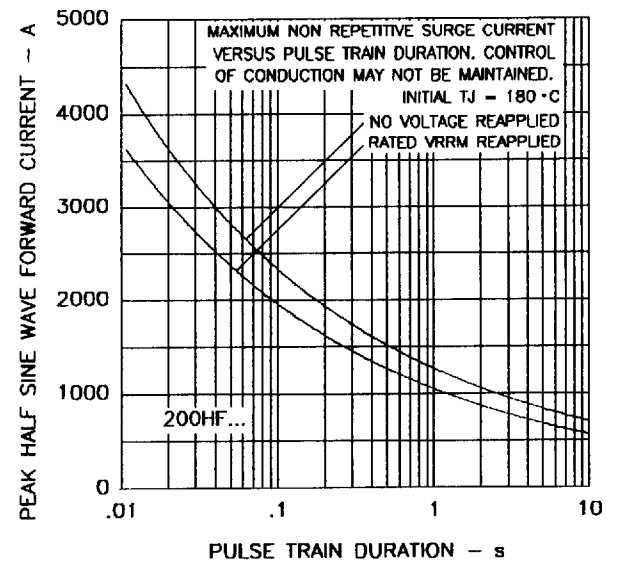


Fig. 13 - FORWARD VOLTAGE DROP CHARACTERISTICS

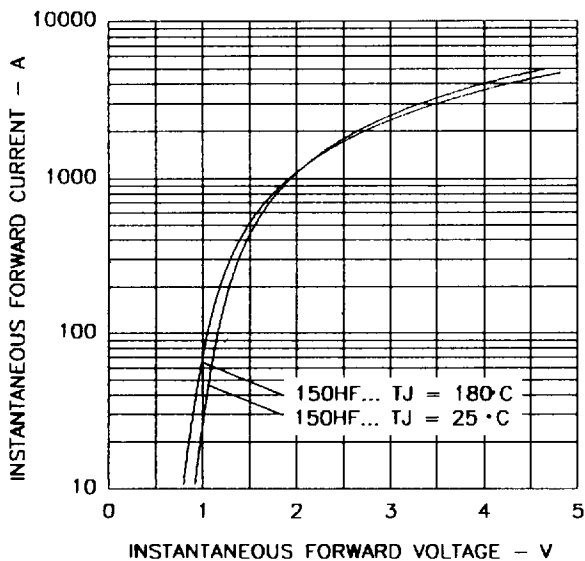
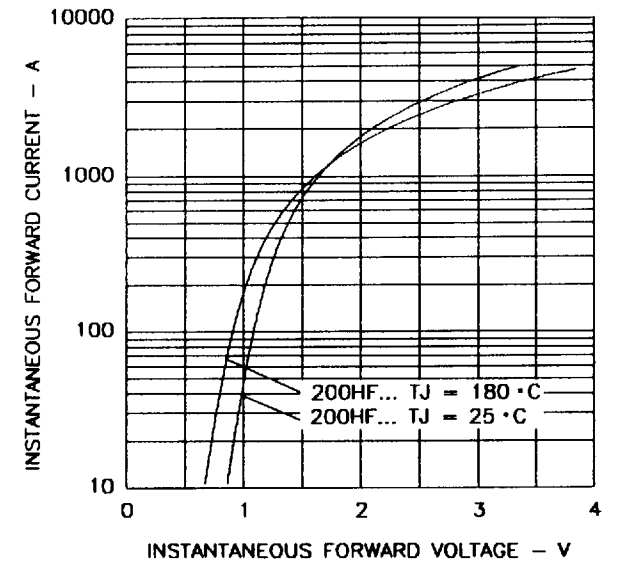


Fig. 14 - FORWARD VOLTAGE DROP CHARACTERISTICS



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Fig. 15 - THERMAL IMPEDANCE Z_{thjc} CHARACTERISTICS

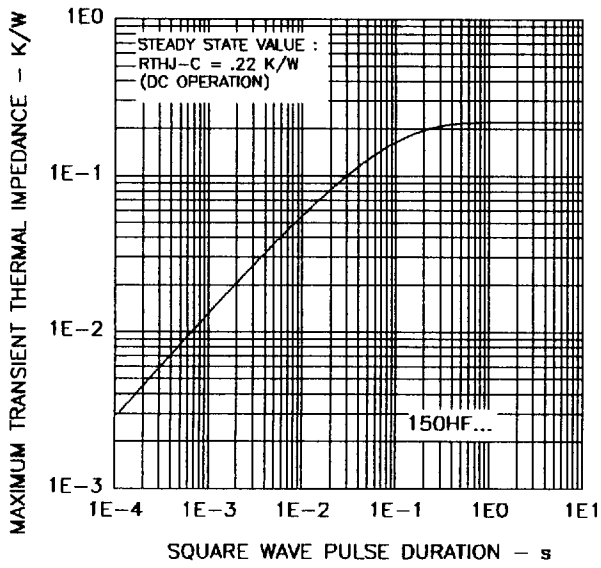


Fig. 16 - THERMAL IMPEDANCE Z_{thjc} CHARACTERISTICS

